



Claims

1. Transistor comprising elements of a bipolar static induction transistor: a gate, a source, a channel and electrodes, and besides one of channels of multielement structure is thicker than other channels, said channel is connected to a separate electrode -- on each of sides of a lightly doped substrate.

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2. Transistor as claimed in claim 1 wherein an epitaxial layer the same conductivity type with the impurity concentration of about 10^{17} cm.^{sup.}-3 is disposed on each of sides of said lightly doped substrate; said gate, said source and said channels are disposed in said epitaxial layer.

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